

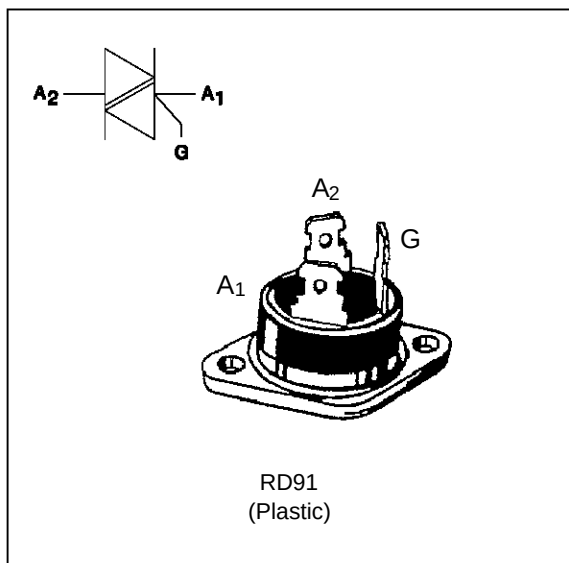
STANDARD TRIACS

FEATURES

- HIGH SURGE CURRENT CAPABILITY
- COMMUTATION : $(dV/dt)_c > 10V/\mu s$
- BTA Family :
INSULATING VOLTAGE = 2500V_(RMS)
(UL RECOGNIZED : E81734)

DESCRIPTION

The BTA25 A/B triac family are high performance glass passivated PNP devices. These parts are suitable for general purpose applications where high surge current capability is required. Application such as phase control and static switching on inductive or resistive load.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
$I_{T(RMS)}$	RMS on-state current (360° conduction angle)	$T_c = 80\text{ }^{\circ}\text{C}$	30	A
I_{TSM}	Non repetitive surge peak on-state current (T_j initial = 25°C)	$t_p = 8.3\text{ ms}$	260	A
		$t_p = 10\text{ ms}$	250	
I_2t	I_2t value	$t_p = 10\text{ ms}$	312.5	A ² s
dI/dt	Critical rate of rise of on-state current Gate supply : $I_G = 500\text{mA}$ $dI_G/dt = 1\text{A}/\mu\text{s}$	Repetitive $F = 50\text{ Hz}$	10	A/ μs
		Non Repetitive	50	
T_{stg} T_j	Storage and operating junction temperature range		- 40 to + 150 - 40 to + 125	$^{\circ}\text{C}$ $^{\circ}\text{C}$
T_l	Maximum lead temperature for soldering during 10 s at 4.5 mm from case		260	$^{\circ}\text{C}$

Symbol	Parameter	BTA25-... A/B				Unit
		400	600	700	800	
V_{DRM} V_{RRM}	Repetitive peak off-state voltage $T_j = 125\text{ }^{\circ}\text{C}$	400	600	700	800	V

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R _{th} (j-c) DC	Junction to case for DC	1.5	°C/W
R _{th} (j-c) AC	Junction to case for 360° conduction angle (F = 50 Hz)	1.1	°C/W

GATE CHARACTERISTICS (maximum values)

P_G (AV) = 1W P_{GM} = 40W (tp = 20 μs) I_{GM} = 8A (tp = 20 μs) V_{GM} = 16V (tp = 20 μs).

ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions		Quadrant		Suffix		Unit
					A	B	
I _{GT}	V _D =12V (DC) R _L =33Ω	T _j =25°C	I-II-III	MAX	100	50	mA
			IV	MAX	150	100	
V _{GT}	V _D =12V (DC) R _L =33Ω	T _j =25°C	I-II-III-IV	MAX	1.5		V
V _{GD}	V _D =V _{DRM} R _L =3.3kΩ	T _j =125°C	I-II-III-IV	MIN	0.2		V
t _{gt}	V _D =V _{DRM} I _G = 500mA dI _G /dt = 3A/μs	T _j =25°C	I-II-III-IV	TYP	2.5		μs
I _L	I _G =1.2 I _{GT}	T _j =25°C	I-III-IV	TYP	70	60	mA
			II		200	180	
I _H *	I _T = 500mA gate open	T _j =25°C		MAX	100	80	mA
V _{TM} *	I _{TM} = 42A tp= 380μs	T _j =25°C		MAX	1.8		V
I _{DRM} I _{RRM}	V _{DRM} Rated V _{RRM} Rated	T _j =25°C		MAX	0.01		mA
		T _j =125°C		MAX	6		
dV/dt *	Linear slope up to V _D =67%V _{DRM} gate open	T _j =125°C		MIN	250		V/μs
(dV/dt) _c *	(dI/dt) _c = 13.3A/ms	T _j =125°C		MIN	10		V/μs

* For either polarity of electrode A2 voltage with reference to electrode A1.

ORDERING INFORMATION

Package	$I_T(\text{RMS})$	$V_{\text{DRM}} / V_{\text{RRM}}$	Sensitivity Specification	
	A	V	A	B
BTA (Insulated)	30	400	X	X
		600	X	X
		700	X	X
		800	X	X

Fig.1 : Maximum RMS power dissipation versus RMS on-state current ($F=50\text{Hz}$).
(Curves are cut off by $(di/dt)_c$ limitation)

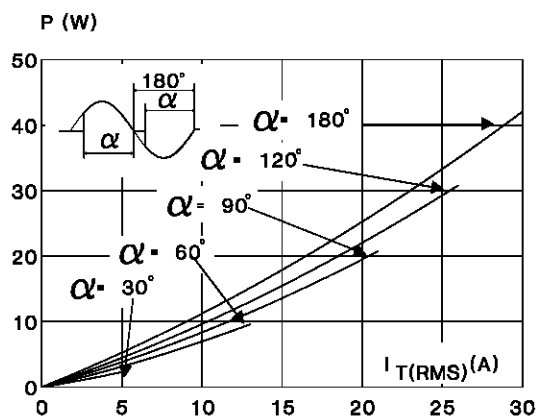


Fig.3 : RMS on-state current versus case temperature.

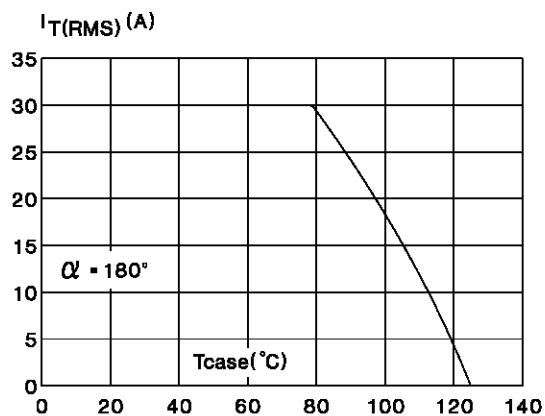


Fig.2 : Correlation between maximum RMS power dissipation and maximum allowable temperatures (T_{amb} and T_{case}) for different thermal resistances heatsink + contact.

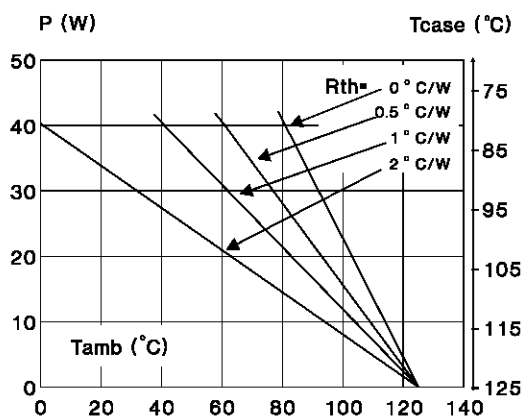


Fig.4 : Relative variation of thermal impedance junction to case versus pulse duration.

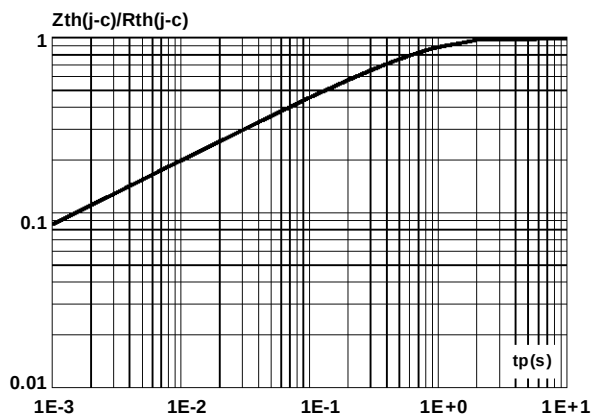


Fig.5 : Relative variation of gate trigger current and holding current versus junction temperature.

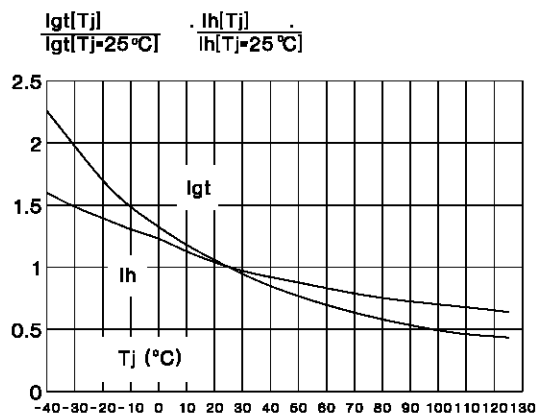


Fig.6 : Non Repetitive surge peak on-state current versus number of cycles.

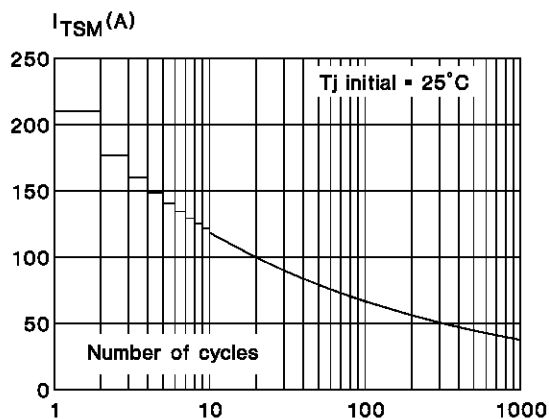


Fig.7 : Non repetitive surge peak on-state current for a sinusoidal pulse with width : $t \leq 10\text{ms}$, and corresponding value of I^2t .

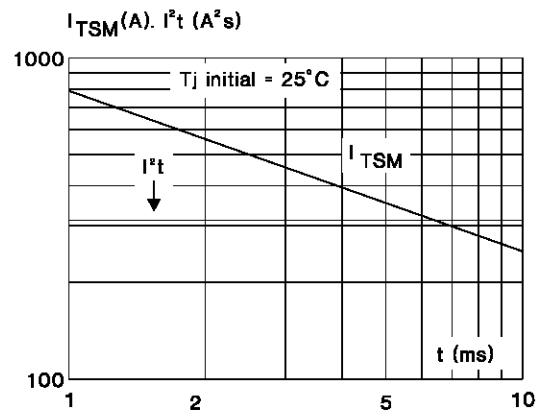
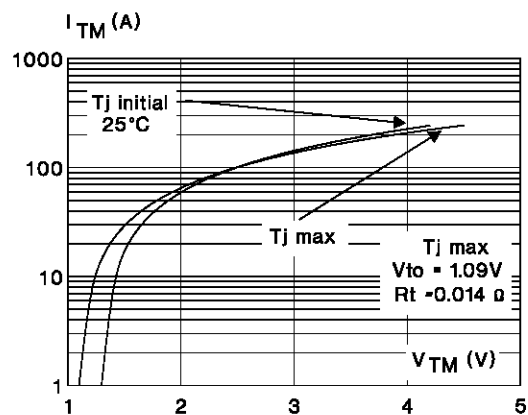
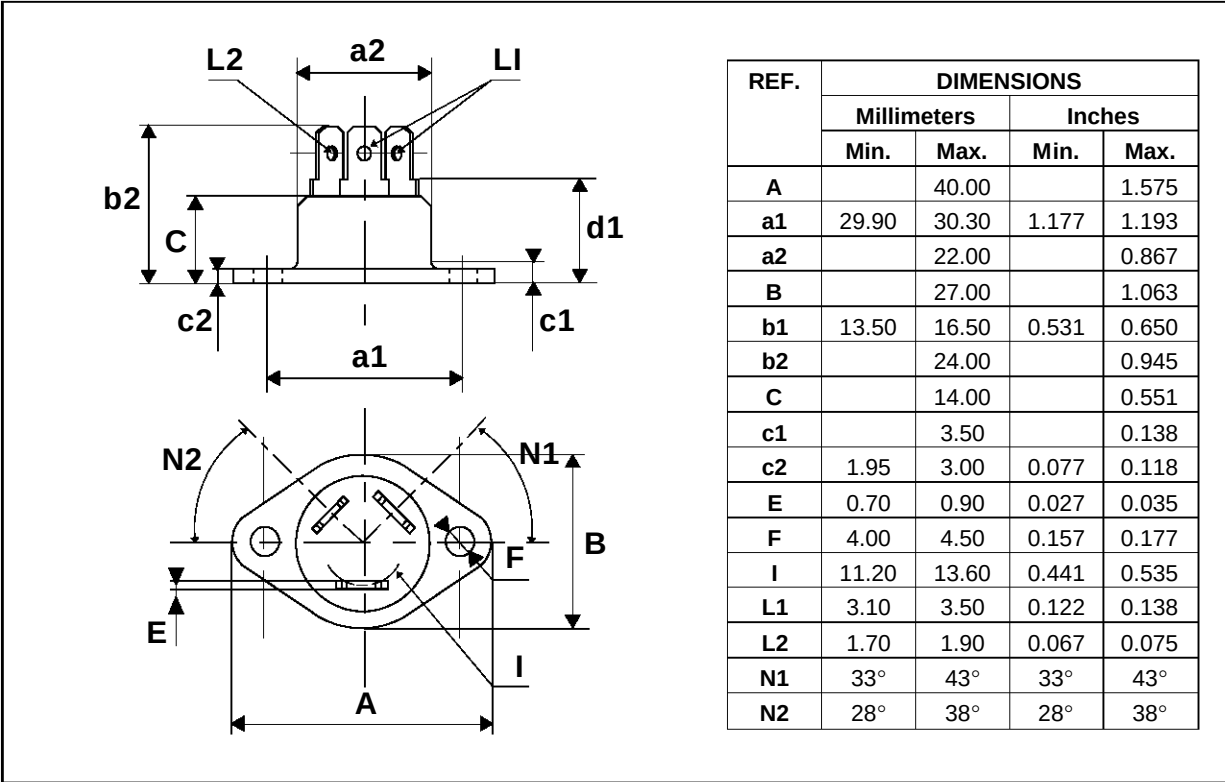


Fig.8 : On-state characteristics (maximum values).



PACKAGE MECHANICAL DATA

RD91 Plastic



Marking : type number
Weight : 20 g

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